

**Product Summary**

The ZMD68203U combines advanced trench MOSFET technology with a low resistance package to provide extremely low  $R_{DS(ON)}$ .

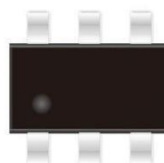


Trench technology  
 $R_{DS(ON)}$  to minimize conductive loss

Dual DIE in one package



Power Management in Notebook Computer,  
 Portable Equipment and Battery Powered  
 Systems



Part NO.	ZMD68203U
Marking	ZMD68203
Packing Information	REEL TAPE
Basic ordering unit (pcs)	3000

$T_C = 25$

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	$V_{DS}$	20	V
Gate-Source Voltage	$V_{GS}$	$\pm 12$	V
Continuous Drain Current	$I_{D@TC=25}$	6.5	A
	$I_{D@TC=75}$	4.9	A
	$I_{D@TC=100}$	4.1	A
Pulsed Drain Current	$I_{DM}$	15	A
Total Power Dissipation( $TC=25$ )	$P_D@TC=25$	3.6	W
Total Power Dissipation( $TA=25$ )	$P_D@TA=25$	0.69	W
Operating Junction Temperature	$T_J$	-55 to 150	
Storage Temperature	$T_{STG}$	-55 to 150	
Single Pulse Avalanche Energy	$E_{AS}$	30	mJ







Fig.7 Switching Time Measurement Circuit

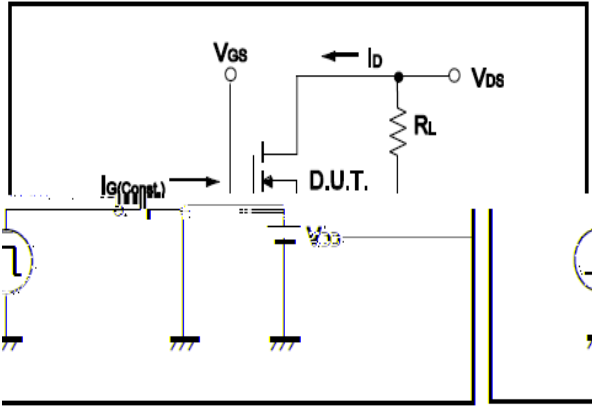


Fig.8 Gate Charge Waveform

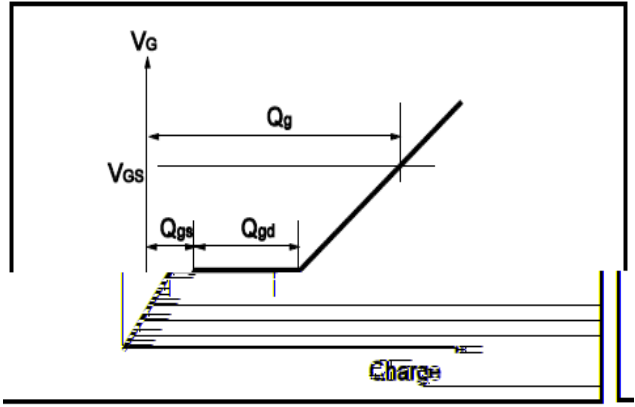


Fig.9 Switching Time Measurement Circuit

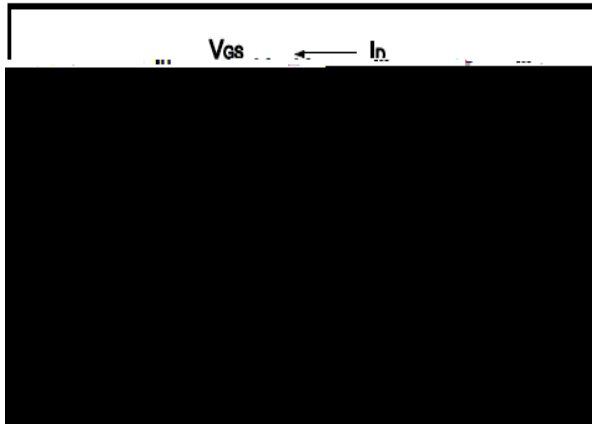


Fig.10 Gate Charge Waveform

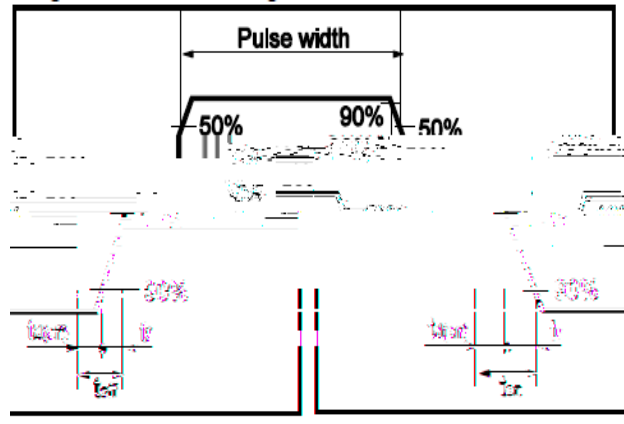


Fig.11 Avalanche Measurement Circuit

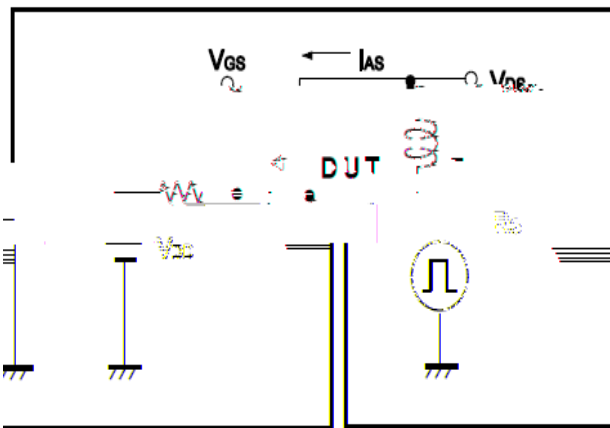
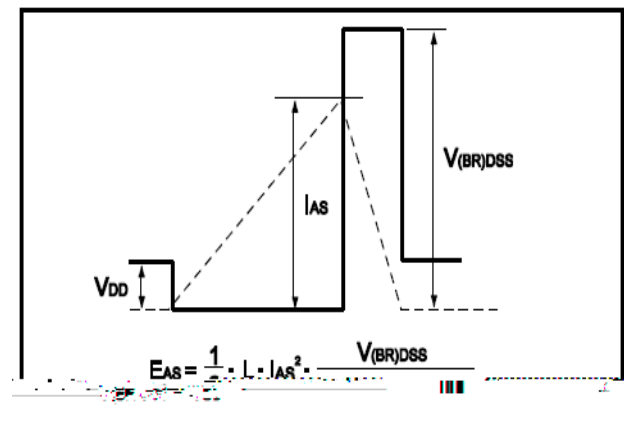


Fig.12 Avalanche Waveform





(SOT23-6)

Unit mm

